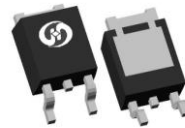
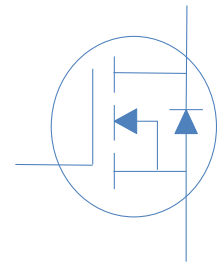


60V N-Ch Power MOSFET

V_{DS}	60	V
$R_{DS(on),typ}$	3.4	m
I_D (Silicon Limited)	144	A
I_D (Package Limited)	70	A



Part Number	Package	Marking
HGD040N06S	TO-252	GD040N06S

Absolute Maximum Ratings at $T_J=25^{\circ}\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	$T_C=25^{\circ}\text{C}$	144	A
		$T_C=100^{\circ}\text{C}$	101	
Continuous Drain Current (Package Limited)		$T_C=25^{\circ}\text{C}$	70	
Drain to Source Voltage	V_{DS}	-	60	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	410	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.3\text{mH}, T_C=25^{\circ}\text{C}$	240	mJ
Power Dissipation	P_D	$T_C=25^{\circ}\text{C}$	150	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	$^{\circ}\text{C}$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	R_{JC}	1	$^{\circ}\text{C}/\text{W}$
Thermal Resistance Junction-Ambient	R_{JA}	46	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics at T_J=25°C (unless otherwise specified)
Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250 A$	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250 A$	2	2.9	4	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=60V, T_J=25^{\circ}C$	-	-	1	A
		$V_{GS}=0V, V_{DS}=60V, T_J=100^{\circ}C$	-	-	100	
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	3.4	4	m
Transconductance	g_{fs}	$V_{DS}=5V, I_D=20A$	-	70	-	S
Gate Resistance	R_G	$V_{GS}=0V, V_{DS}$ Open, $f=1MHz$	-	1.5	-	

Dynamic Characteristics

Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=30V, f=1MHz$	-	3487	-	pF
Output Capacitance	C_{oss}		-	984	-	
Reverse Transfer Capacitance	C_{rss}		-	40	-	
Total Gate Charge (10V)	$Q_g (10V)$	$V_{DD}=30V, I_D=20A, V_{GS}=10V$	-	53	-	nC
Gate to Source Charge	Q_{gs}		-	17	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	11	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=20A, V_{GS}=10V, R_G=10 \Omega$	-	13	-	ns
Rise time	t_r		-	10	-	
Turn off Delay Time	$t_{d(off)}$		-	52	-	
Fall Time	t_f		-	13	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R=30V, I_F=20A, di_F/dt=300A/s$	-	40	-	ns
Reverse Recovery Charge	Q_{rr}		-	70	-	nC

Fig 1. Typical Output Characteristics

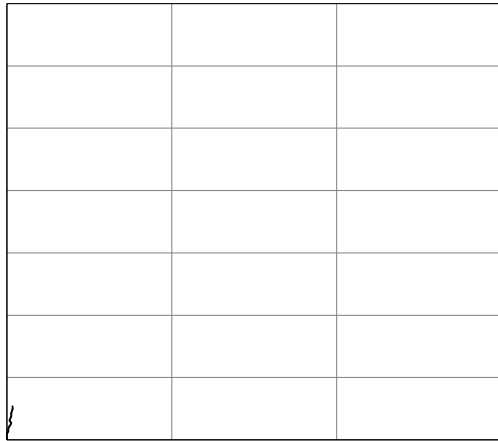


Figure 2. On-Resistance vs. Gate-Source Voltage

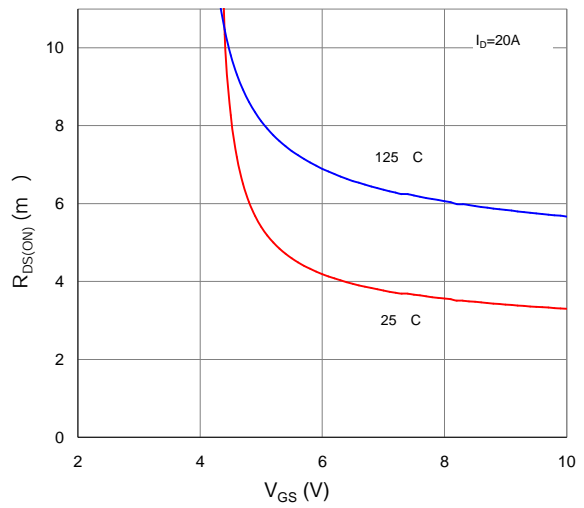


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

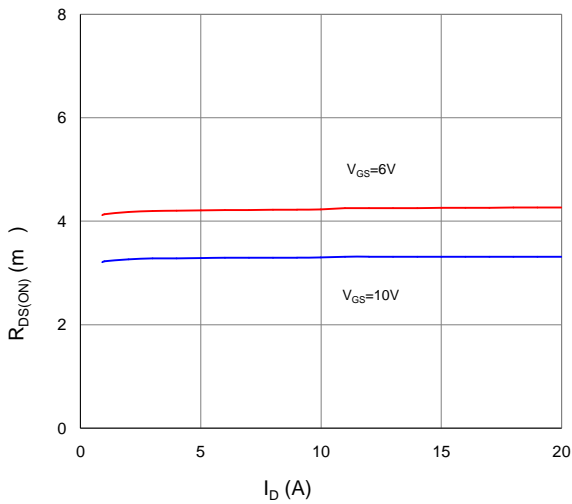


Figure 4. Normalized On-Resistance vs. Junction Temperature

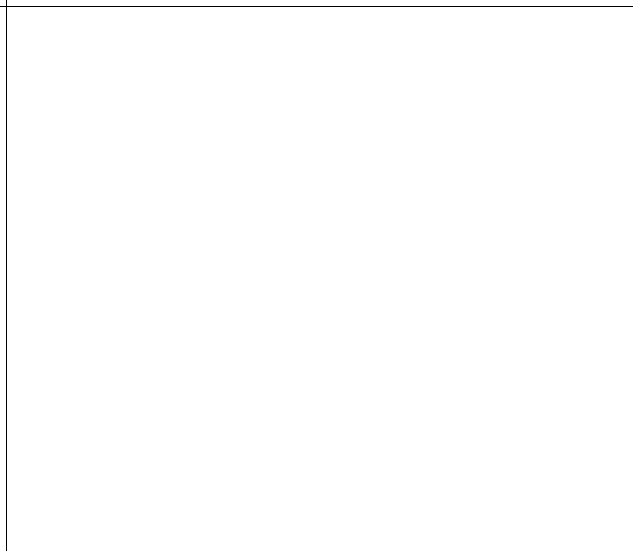


Figure 5. Typical Transfer Characteristics

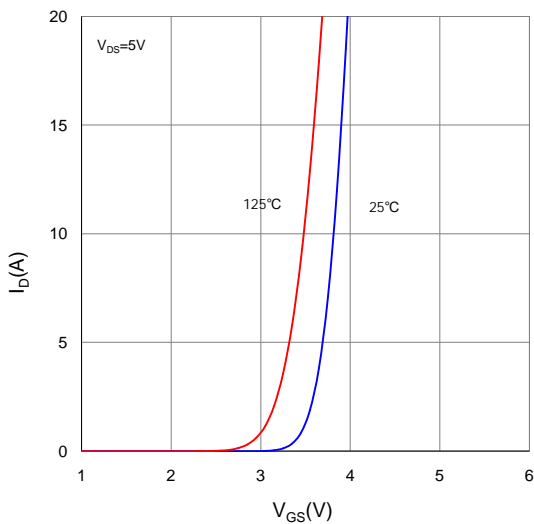


Figure 6. Typical Source-Drain Diode Forward Voltage

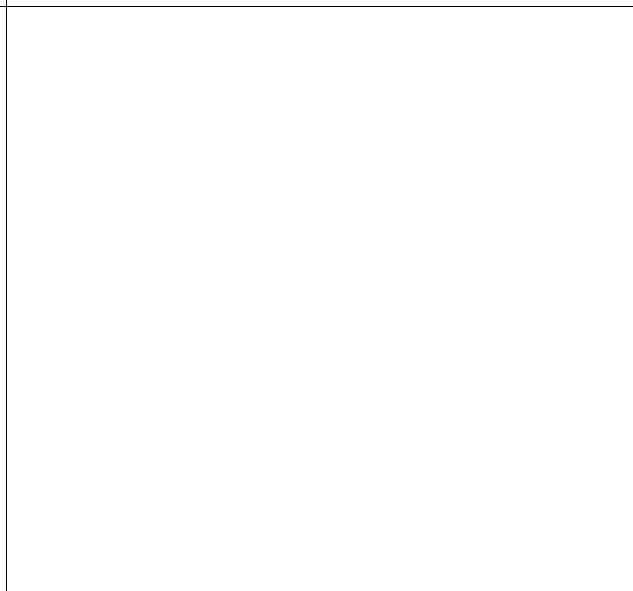


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

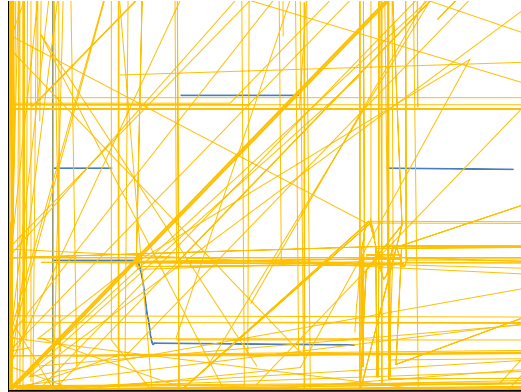
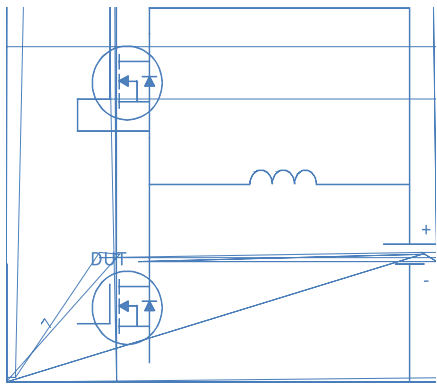
Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

Figure 9. Maximum Safe Operating Area

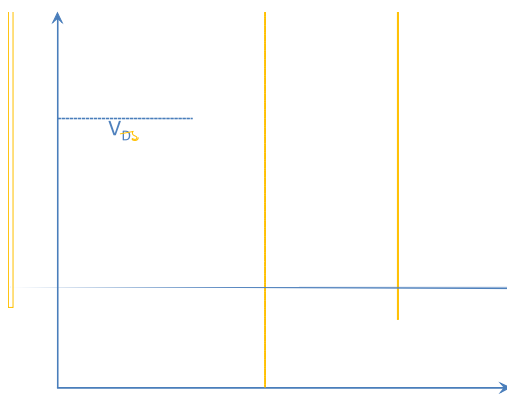
Figure 10. Maximum Drain Current vs. Case Temperature

1. Normalized Maximum Transient Thermal Impedance, Junction-to-Case

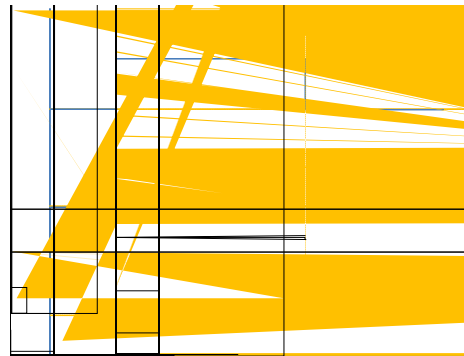
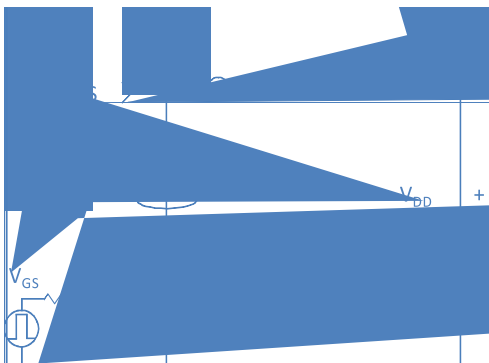
Inductive switching Test



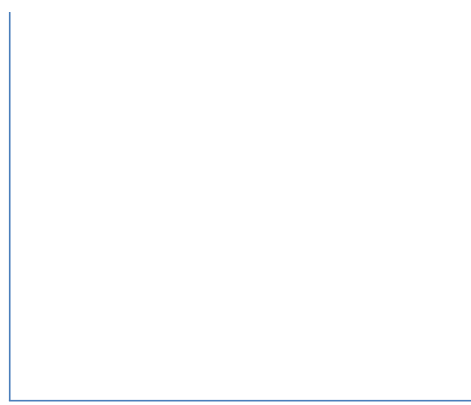
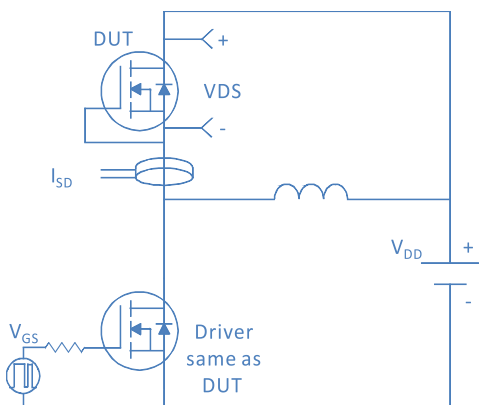
Gate Charge Test



Unclamped Inductive Switching (UIS) Test

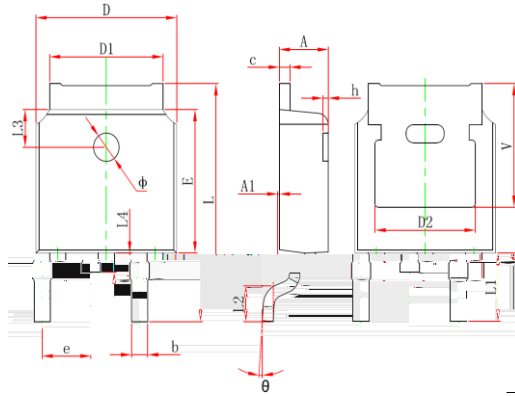


Diode Recovery Test



Package Outline

TO-252, 2 leads



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.095
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.480	0.500	0.019	0.020
D	4.800	5.000	0.189	0.197
D1	1.000	1.100	0.039	0.043
D2	4.600	4.800	0.181	0.189
E	0.760	0.860	0.030	0.034
L	2.900	3.100	0.114	0.122
L1	1.700	0.055	0.067	1.490
L2	REF.	0.063-REF.	REF.	1.600
L3	REF.	0.030	REF.	0.001
L4	REF.	0.030	REF.	0.001
e	8	8	0	0
theta	0.300	0.000	0.012	0.000
V	3.350-REF.	0.241-REF.	REF.	REF.

